Old Company Name in Catalogs and Other Documents

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Renesas Electronics website: http://www.renesas.com

April 1st, 2010 Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

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Renesas

MOS FIELD EFFECT TRANSISTOR

μ PA2794AGR

SWITCHING N- AND P-CHANNEL POWER MOS FET

DESCRIPTION

The µPA2794AGR is N- and P-channel MOS Field Effect Transistors designed for Motor Drive application.

FEATURES

- Low on-state resistance
- N-channel $R_{DS(on)1} = 25 \text{ m}\Omega \text{ MAX}$. (Vgs = 10 V, ID = 2.8 A) $R_{DS(on)2} = 33 \text{ m}\Omega \text{ MAX.}$ (Vgs = 4.5 V, ID = 2.8 A) P-channel $R_{DS(on)1} = 43 \text{ m}\Omega \text{ MAX.}$ (Vgs = -10 V, Ip = -2.8 A)

 $R_{DS(on)2} = 54 \text{ m}\Omega \text{ MAX.}$ (Vgs = -4.5 V, ID = -2.8 A)

Low input capacitance

N-channel Ciss = 2200 pF TYP.

- P-channel Ciss = 2200 pF TYP.
- Built-in gate protection diode
- Small and surface mount package (Power SOP8)

ORDERING INFORMATION							
PART NUMBER	LEAD PLATING	PACKING	PACKAGE				
μ PA2794AGR-E1-AT ^{Note}							
μPA2794AGR-E2-AT ^{Note}	Pure Sn	Tape 2500 p/reel	Power SOP8				

Note Pb-free (This product does not contain Pb in external electrode and other parts.)

EQUIVALENT CIRCUITS

N-channel P-channel Drain Drain Body Body Gate Diode Gate Diode Gate Gate Protection Protection Source Source Diode Diode

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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N-channel Source 1 1 Gate 1 7, 8: Drain 1 P-channel 3 Source 2 4 : Gate 2 5, 6: Drain 2 ()Н 6.0 ±0.3 4.4 5.37 MAX. 0.8 4 .8 MAX 00 S 0.5 ± 0.2 Z 0.10 1.27 0.78 MAX 0.05 | 0.40 + 0.10 - 0.050.12 M

PACKAGE DRAWING (Unit: mm)

ABSOLUTE MAXIMUM RATINGS (TA = 25°C. All terminals are connected.)

PARAMETER	SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
Drain to Source Voltage (VGs = 0 V)	'gs = 0 V) VDSS 60 -60		V	
Gate to Source Voltage (V _{DS} = 0 V)	Vgss	±20	∓20	V
Drain Current (DC)	ID(DC)	±5.5	∓5.5	А
Drain Current (pulse) Note1	D(pulse)	±22	∓22	А
Total Power Dissipation (1 unit) Note2	P _{T1}	1.7		W
Total Power Dissipation (2 units) Note2	Pt2	2.0 150		W
Channel Temperature	Tch			°C
Storage Temperature	Tstg	-55 to +150		°C
Single Avalanche Current ^{Note3}	las	5.5	-5.5	А
Single Avalanche Energy Note3	Eas	3.03		mJ

Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Mounted on ceramic substrate of 2000 $\text{mm}^2 \times 1.6 \text{ mm}$

3. Starting T_{ch} = 25°C, V_{DD} = 30 V, R_G = 25 Ω , L = 100 μ H, V_{GS} = 20 \rightarrow 0 V

ELECTRICAL CHARACTERISTICS (TA = 25°C. All terminals are connected.)

N-channel

NEC

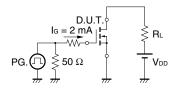
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	loss	V _{DS} = 60 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	lgss	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5	2.0	2.5	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10 V, I _D = 2.8 A	4	7.6		S
Drain to Source On-state Resistance ^{Note}	RDS(on)1	V _{GS} = 10 V, I _D = 2.8 A		19.5	25	mΩ
	RDS(on)2	V _{GS} = 4.5 V, I _D = 2.8 A		23	33	mΩ
Input Capacitance	Ciss	V _{DS} = 10 V,		2200		pF
Output Capacitance	Coss	V _{GS} = 0 V,		245		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		136		pF
Turn-on Delay Time	td(on)	V _{DD} = 30 V, I _D = 2.8 A,		10		ns
Rise Time	tr	V _{GS} = 10 V,		16		ns
Turn-off Delay Time	td(off)	R _G = 0 Ω		58		ns
Fall Time	tr			7.5		ns
Total Gate Charge	Q _G	I _D = 5.5 A,		41		nC
Gate to Source Charge	Q _{GS}	V _{DD} = 48 V,		6.3		nC
Gate to Drain Charge	Qgd	V _{GS} = 10 V		11		nC
Body Diode Forward Voltage ^{Note}	VF(S-D)	I _F = 5.5 A, V _{GS} = 0 V		0.8	1.5	V
Reverse Recovery Time	trr	IF = 5.5 A, VGS = 0 V,		28		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/ <i>µ</i> s		29		nC

Note Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY

D.U.T ấг Rg = 25 Ω ~~~~ \leq 50 Ω PG. V_{DD} $V_{\text{GS}} = 20 \rightarrow 0 \ V$ BVDSS las VDD -Starting Tch

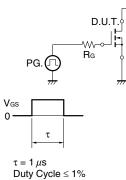
TEST CIRCUIT 3 GATE CHARGE

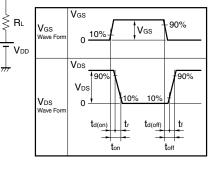


TEST CIRCUIT 2 SWITCHING TIME

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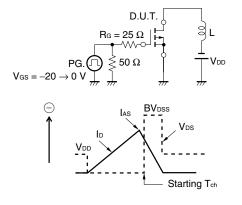
P-channel

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = -60 V, V _{GS} = 0 V			-10	μA
Gate Leakage Current	lgss	V _{GS} = ∓20 V, V _{DS} = 0 V			∓10	μA
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1 mA	-1.0	-1.7	-2.5	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = -10 V, I _D = -2.8 A	5	10		S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = -10 V, I _D = -2.8 A		33	43	mΩ
	RDS(on)2	V _{GS} = -4.5 V, I _D = -2.8 A		36	54	mΩ
Input Capacitance	Ciss	V _{DS} = -10 V,		2200		pF
Output Capacitance	Coss	V _{GS} = 0 V,		270		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		200		pF
Turn-on Delay Time	td(on)	$V_{DD} = -30 \text{ V}, \text{ I}_{D} = -2.8 \text{ A},$		10		ns
Rise Time	tr	V _{GS} = -10 V,		22		ns
Turn-off Delay Time	td(off)	R _G = 0 Ω		150		ns
Fall Time	tr			23		ns
Total Gate Charge	QG	I _D = -5.5 A,		45		nC
Gate to Source Charge	QGS	$V_{DD} = -48 V,$		4.3		nC
Gate to Drain Charge	QGD	V _{GS} = -10 V		13		nC
Body Diode Forward Voltage Note	VF(S-D)	IF = 5.5 A, VGS = 0 V		0.83	1.5	V
Reverse Recovery Time	trr	$I_F = -5.5 \text{ A}, \text{ V}_{GS} = 0 \text{ V},$		46		ns
Reverse Recovery Charge	Qrr	di/dt = –50 A/µs		29		nC

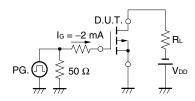
Note Pulsed

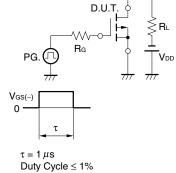
TEST CIRCUIT 1 AVALANCHE CAPABILITY

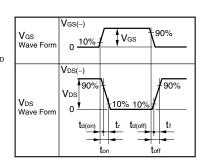
TEST CIRCUIT 2 SWITCHING TIME



TEST CIRCUIT 3 GATE CHARGE



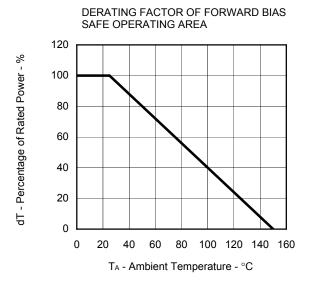




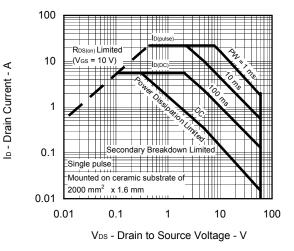
TYPICAL CHARACTERISTICS (TA = 25°C)

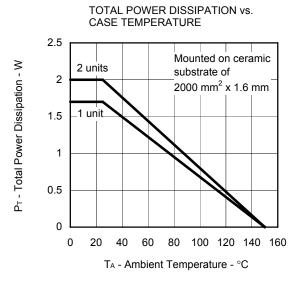
(1) N-channel

NEC

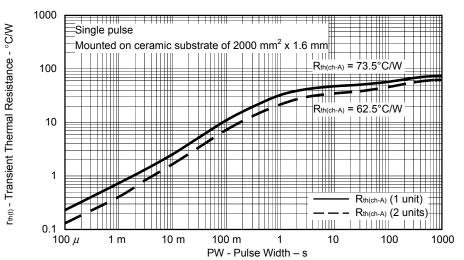


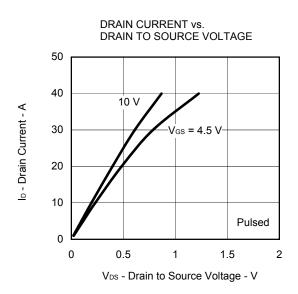




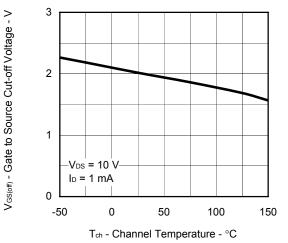






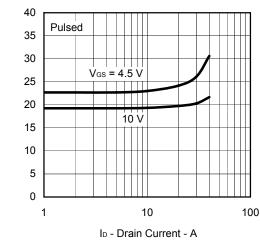




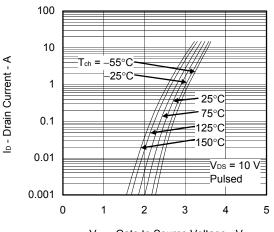




DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

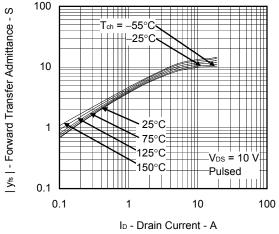


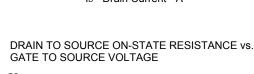
FORWARD TRANSFER CHARACTERISTICS

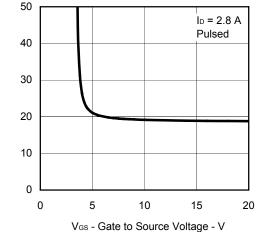


VGS - Gate to Source Voltage - V

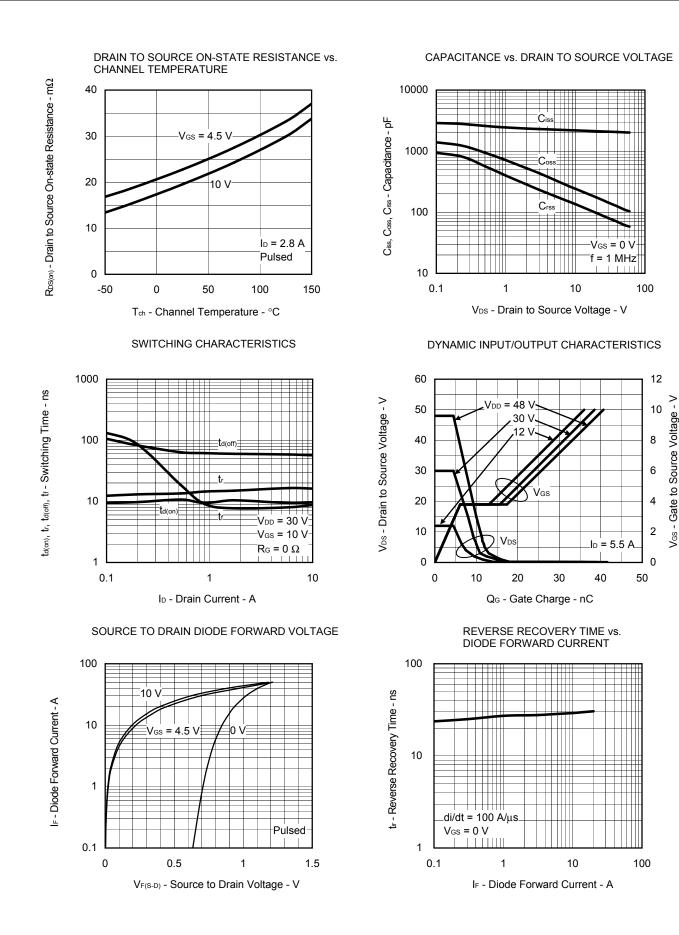
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



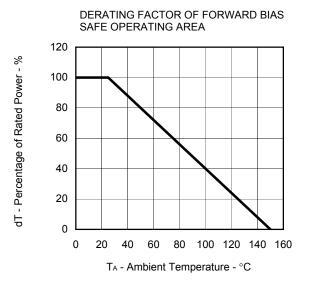




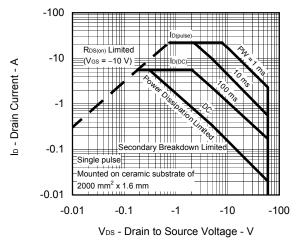
 $R_{DS(cn)}$ - Drain to Source On-state Resistance - $m\Omega$

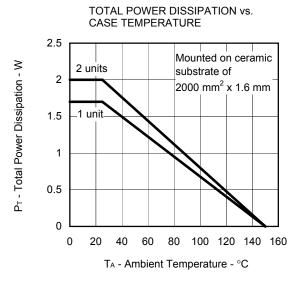


(2) P-channel

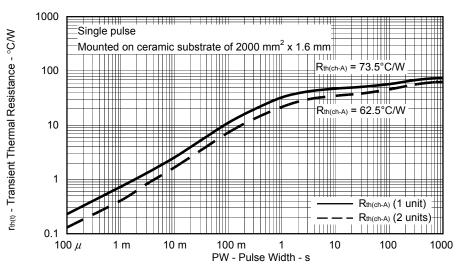


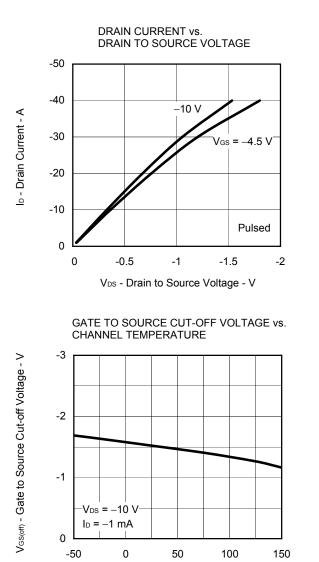
FORWARD BIAS SAFE OPERATING AREA





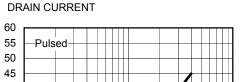
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



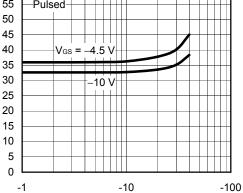


Tch - Channel Temperature - °C



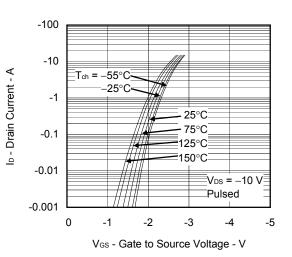


DRAIN TO SOURCE ON-STATE RESISTANCE vs.

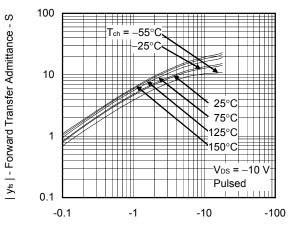




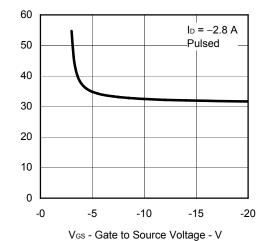
FORWARD TRANSFER CHARACTERISTICS



FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT







DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

 $R_{DS(on)}$ - Drain to Source On-state Resistance - $m\Omega$

ν

-100

-12

-10

-8

-6

-4

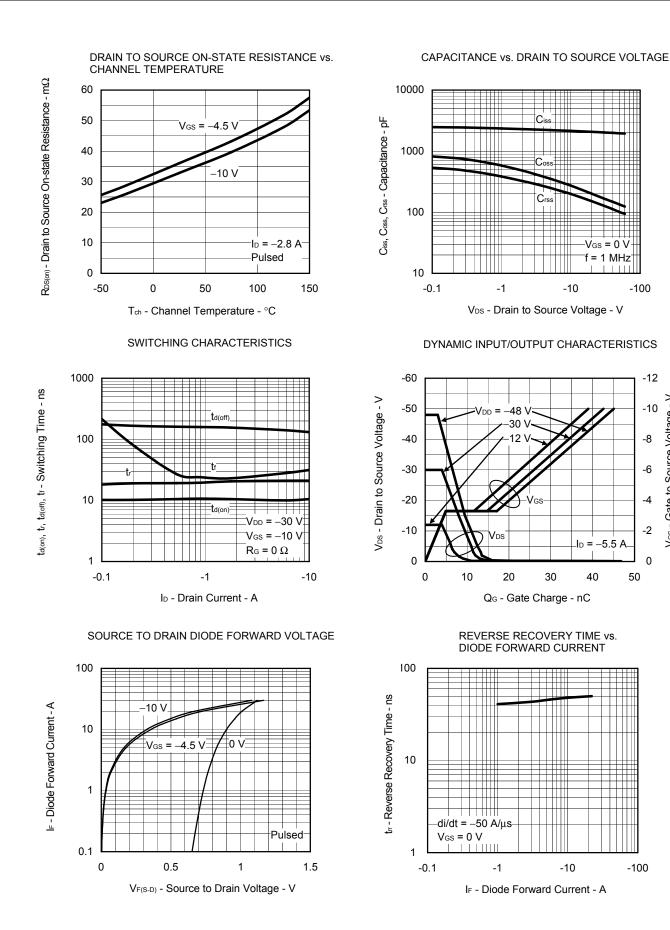
-2

0

50

-100

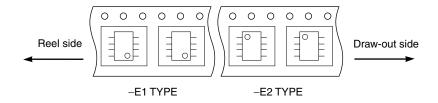
V_{GS} - Gate to Source Voltage - V



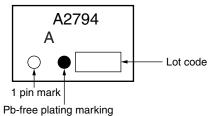
TAPE INFORMATION

NEC

There are two types (-E1, -E2) of taping depending on the direction of the device.



MARKING INFORMATION



RECOMMENDED SOLDERING CONDITIONS

The μ PA2794AGR should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, please contact an NEC Electronics sales representative.

For technical information, see the following website.

Semiconductor Device Mount Manual (http://www.necel.com/pkg/en/mount/index.html)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	d reflow Maximum temperature (Package's surface temperature): 260°C or below	
	Time at maximum temperature: 10 seconds or less	
	Time of temperature higher than 220°C: 60 seconds or less	
	Preheating time at 160 to 180°C: 60 to 120 seconds	
	Maximum number of reflow processes: 3 times	
	Maximum chlorine content of rosin flux (percentage mass): 0.2% or less	
Partial heating	Maximum temperature (Pin temperature): 350°C or below	P350
	Time (per side of the device): 3 seconds or less	
	Maximum chlorine content of rosin flux: 0.2% (wt.) or less	

Caution Do not use different soldering methods together (except for partial heating).

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